

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Withdrawn) A ferroelectric layer including space charges,
wherein the space charges show a concentration peak at least at one of an upper portion and a lower portion of the ferroelectric layer in a direction of the thickness of the ferroelectric layer.
2. (Withdrawn) The ferroelectric layer as defined in claim 1, wherein:
the space charges show a concentration peak at the upper portion and the lower portion of the ferroelectric layer; and
the polarities of the space charges at the upper and lower portions are different from each other.
3. - 4. (Canceled)
5. (Currently Amended) A method of manufacturing a ferroelectric layer, comprising:
forming a first ferroelectric section in which crystal defects are intentionally created, by using a first material used for forming a ferroelectric in which part of substances in a stoichiometric composition is absent; and
forming, over the first ferroelectric section, a second ferroelectric section which has less crystal defects than the first ferroelectric section, by using a second material used for forming a ferroelectric which is closer to the stoichiometric composition compared to the ferroelectric which is formed by using the first material.
~~forming a first ferroelectric section including space charges generated by causing a crystal defect to occur; and~~
~~forming a second ferroelectric section over the first ferroelectric section.~~

6. (Currently Amended) The method of manufacturing a ferroelectric layer as defined in claim 5, further comprising:

forming a third ferroelectric section including space charges generated by causing a crystal defect to occur over the second ferroelectric section,

~~wherein the polarities of the space charges in the first ferroelectric section and the third ferroelectric section are~~being different from each other.

7.-10. (Canceled)

11. (Currently Amended) A method of manufacturing a ferroelectric layer, comprising:

forming a first ferroelectric section in which crystal defects are intentionally created, by performing crystallization heat treatment for first oxygen partial pressure, and

forming a second ferroelectric section which has less crystal defects than the first ferroelectric section, by performing crystallization heat treatment for second oxygen partial pressure which is greater than the first oxygen partial pressure.~~The method of manufacturing a ferroelectric layer as defined in claim 5,~~

~~wherein the crystal defect is caused by crystallization heat treatment in which oxygen partial pressure is controlled.~~

12. (Currently Amended) A method of manufacturing a ferroelectric layer, comprising:

forming a first ferroelectric section in which crystal defects are intentionally formed by introducing impurities, and

forming a second ferroelectric section which has less crystal defects than the first ferroelectric section~~The method of manufacturing a ferroelectric layer as defined in claim 5,~~

~~wherein the crystal defect is caused by introducing impurities.~~

13. (Withdrawn) A ferroelectric capacitor comprising the ferroelectric layer as defined in claim 1.
14. (Withdrawn) A ferroelectric capacitor comprising the ferroelectric layer as defined in claim 2.
15. (Withdrawn) A ferroelectric memory comprising the ferroelectric capacitor as defined in claim 13.
16. (Withdrawn) A ferroelectric memory comprising the ferroelectric capacitor as defined in claim 14.
17. (Withdrawn) The ferroelectric memory as defined in claim 15,
wherein the ferroelectric memory is operated by nondestructive readout.
18. (Withdrawn) The ferroelectric memory as defined in claim 16,
wherein the ferroelectric memory is operated by nondestructive readout.
19. (New) The method of manufacturing a ferroelectric layer as defined in claim 5, wherein the first and second ferroelectric sections are formed by a vapor phase method.
20. (New) The method of manufacturing a ferroelectric layer as defined in claim 11, wherein the first oxygen partial pressure is set at 0.02 MPa or less.
21. (New) The method of manufacturing a ferroelectric layer as defined in claim 12, wherein impurities are introduced, by adding the impurities to a material which is used for forming a ferroelectric.
22. (New) The method of manufacturing a ferroelectric layer as defined in claim 5, wherein the crystal defects formed in the first ferroelectric section cause a positive or negative effective charge to be generated in a ferroelectric.